

## **ABSTRACT OF THE DISCLOSURE**

**[30]** Aspects of the method for reducing noise in the substrate may comprise doping a substrate with a first dopant and doping a first well disposed on the substrate with a second dopant. The first well may be a deep well. A second well disposed within the first well may be doped with a second dopant. A first transistor having a first transistor channel type and one or more transistor components may be disposed within the second well. A quiet voltage source may be coupled to a body of the first transistor. A third well disposed within the first well may be doped with the first dopant. A second transistor having a second transistor type and one or more transistor components may be disposed within the third well. In this arrangement, disposing the first well between the substrate and the second well may reduce noise in the substrate.